



200G per Lane for beyond 400GbE

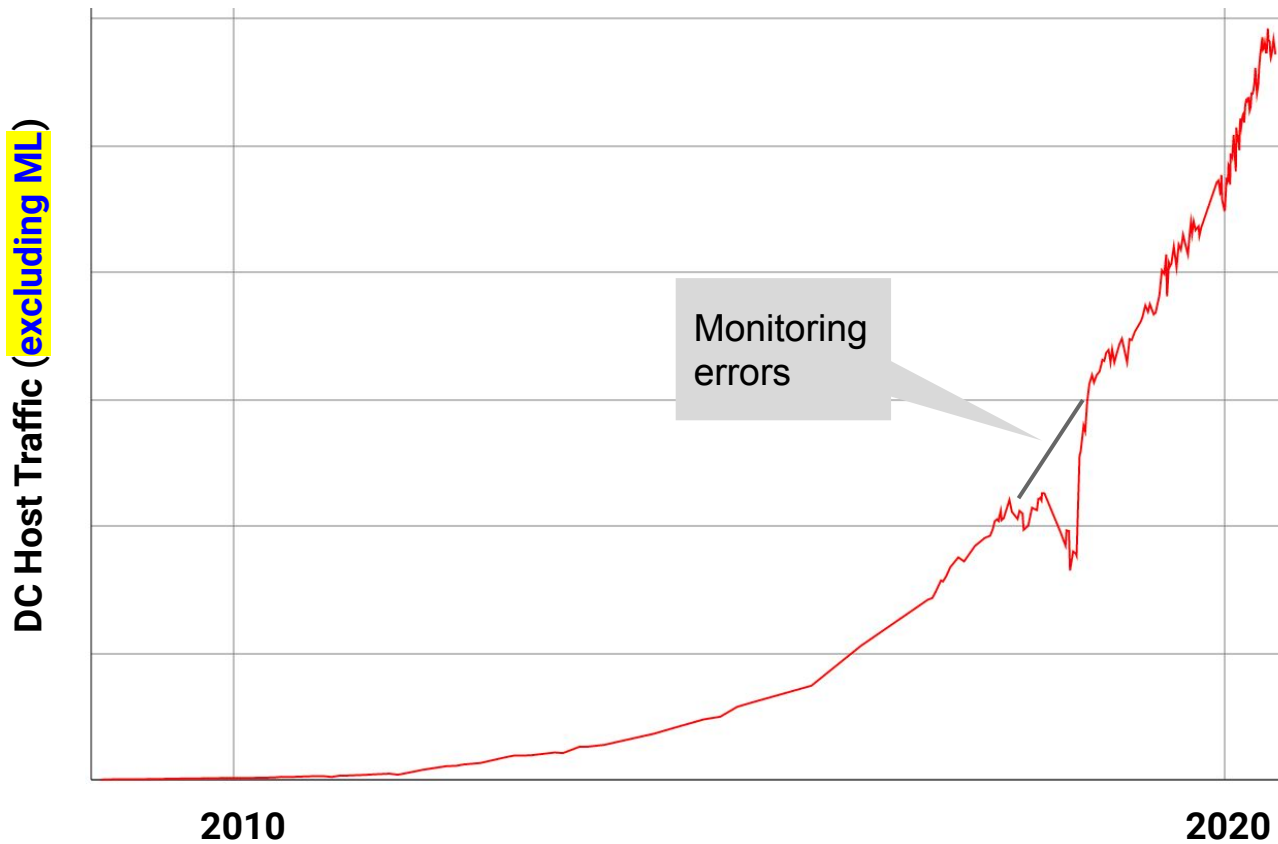
Cedric Lam, Xiang Zhou, and Hong Liu

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IEEE 802.3 NEA Meeting

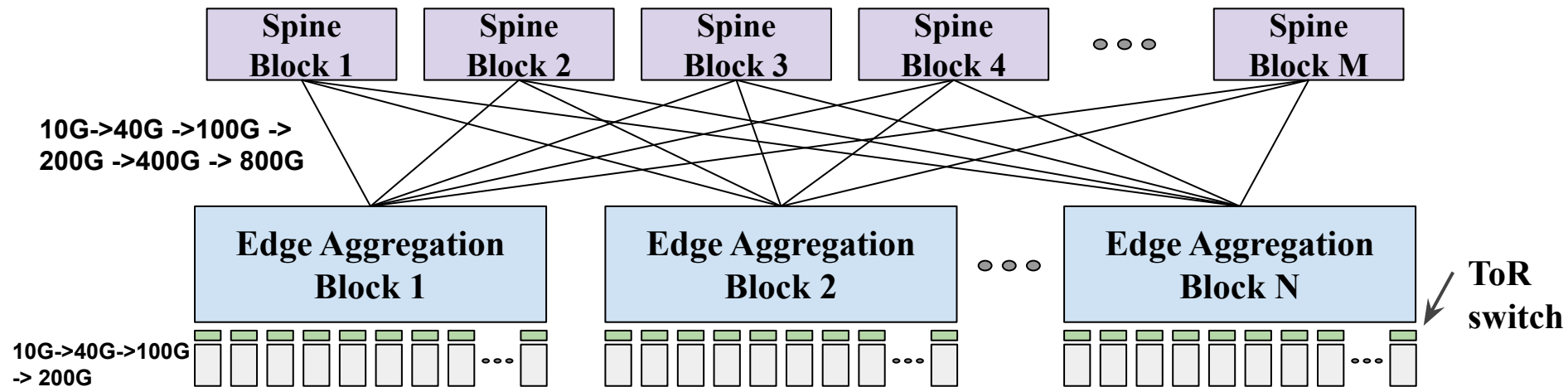
Outline

- Driver and use cases for beyond 400G
- Justification for 200G per lane
 - Lower TCO
 - Scalability to 1.6T Ethernet
- 200G optical lane technical feasibilities
 - Baseline performance for different modulation format choices
 - Key component requirements
 - 200G per lane (optical) components readiness survey

DC Traffic Continues to Grow Rapidly (Regular Servers)



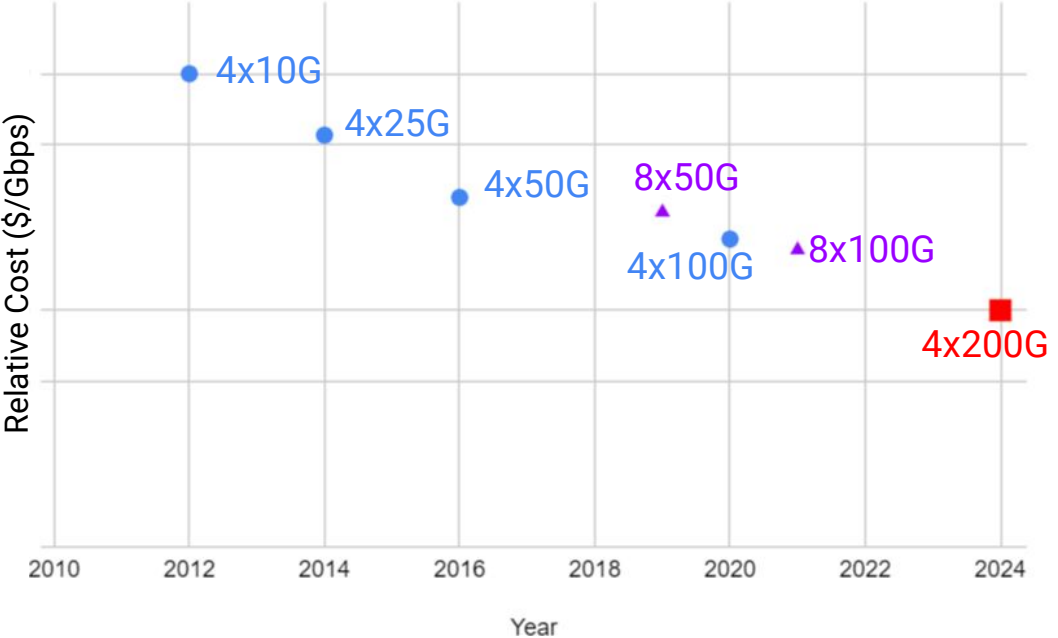
> 400GbE will be needed in DCN Fabrics



Why 200G per Lane?

- Cost efficiency for 800G
- Path to 1.6Tb per port

Cost/Gbps vs. Speed per Optical Lane



- **Faster optical lane speed is key to lower costs, but needs to align with electrical I/O speed for best cost & power efficiency**

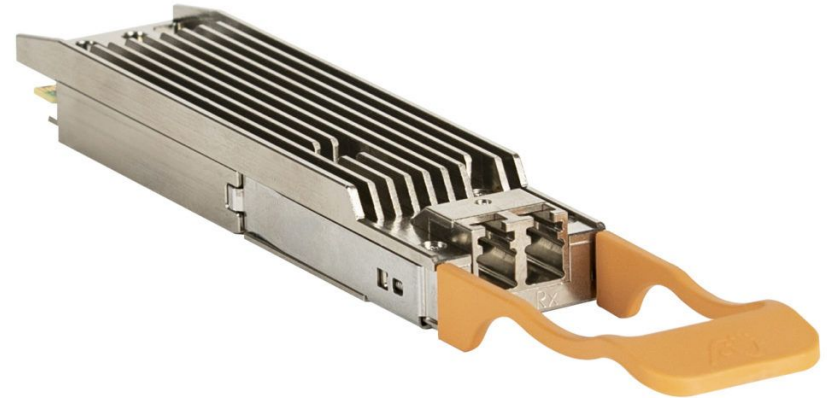
Implementation Comparison of 800G

	IM-DD PAM (8 lanes)	IM-DD PAM (4 lanes)
Baud Rate (Gbaud)	56G	~112G
Number of Lasers	8	4
MZMs and Drivers	8	4
PD/TIAs	8	4
Relative DSP power	1	~1.1 (stronger FEC and DSP)
Link distance	Limited by dispersion (2km, CWDM8)	Limited by dispersion (< 1km*, CWDM4)
Fan out granularity	100Gb/s	200Gb/s
Scale to 1.6Tb/s and beyond	No	Yes

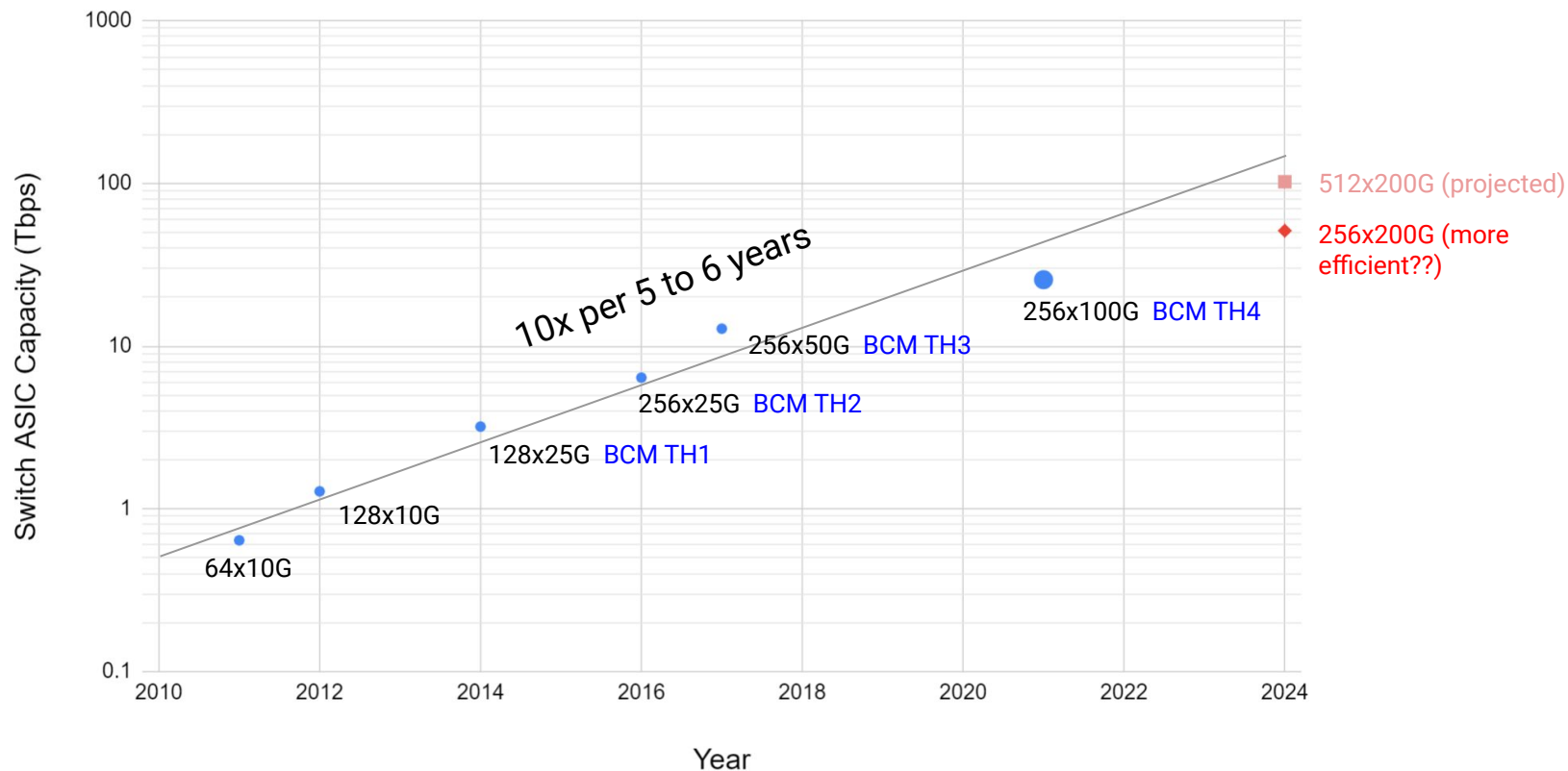
* Reach may be extended by more powerful DSP such as MLSE (Ilya Lyubomirsky, IEEE 2020 summer topical talk)

Necessity of 200Gbps Electrical Lanes

- Scalability and visibility into 1.6T Ethernet
 - OSFP defined 8 electrical lanes
 - 8x 200G gives us 1.6 capacity
- Enable 100Tbps Switch ASIC
- Matching the electrical lane speed w/ optical lane speed
 - Simplifies module architectures
 - Reduces overall power consumption
 - Keeps the cost down in the long run



100Tbps Switch ASIC in 4 Years





200G Optical Lane Technical Feasibilities

System Model

Focus on the following Functions/Blocks

- Two candidate modulation formats: PAM4 and PAM6
- 2 types of transmitters
 - InP EML
 - SiP MZM
- PD + TIA: $R=0.8\text{A/W}$, $\text{IRN}=16\text{pA}/\sqrt{\text{Hz}}$
- Digital Electronics
 - 6-tap Tx FFE, 17-tap Rx-FFE, T-spaced
 - **FEC threshold $4\text{e-}3$ assumed for 200Gb/s per lane***

* Ilya Lyubomirsky, "Coherent vs. Direct Detection for Next Generation Intra-Datacenter Optical Interconnects," IEEE 2020 summer topical

Overall comparison: PAM4 vs PAM6

	PAM4	PAM6
Baud rate	~113Gbaud	~90Gbaud
Rx sensitivity penalty ^A @45GHz BW	~4.9dB	~3.3dB
Rx sensitivity penalty ^A @50GHz BW	~2.3dB	~2.4dB
Rx sensitivity penalty ^A @55GHz BW	~1.6dB	~2.2dB
Support 1km O-CWDM4 CD with EML	Yes CD penalty<1.5dB@55GHz	Yes CD penalty<1dB@55GHz
DAC/ADC ENOB requirement	~5.5 (stronger EQ)	~5.5 (higher-order mod.)
Relative DSP power	1	<1 ?

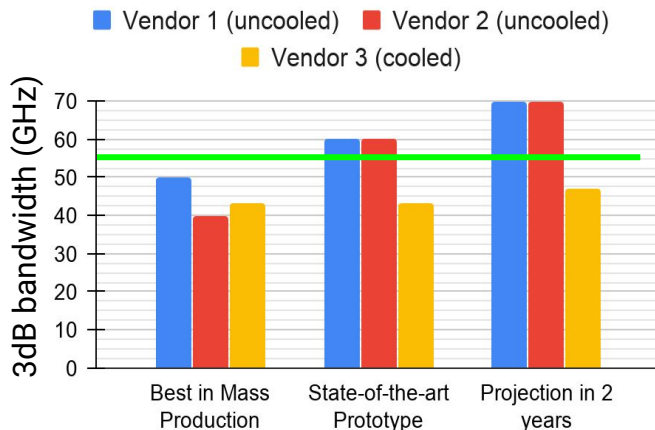
^A: Compared to 106Gb/s per lane PAM4 with KP4 FEC

- If PAM6 can achieve lower power, a dual-mode PAM4/PAM6 may be considered
 - PAM4 only for difficult links (higher link loss and/or MPI)
 - PAM6 for majority of the normal links to save overall network power

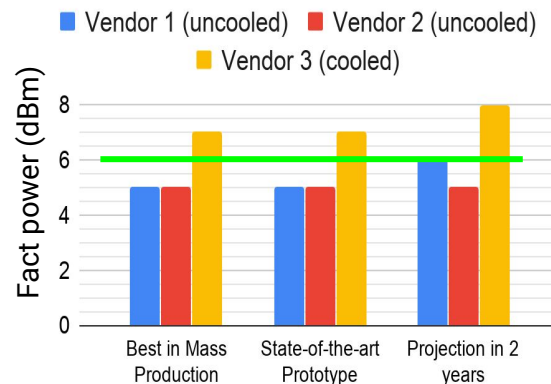
200Gb/s per optical lane components survey

Transmitter 1: InP EML

3-dB Bandwidth



Facet power (modulated)



— Preliminary requirements guideline to support 1km 800G CWDM4 reach

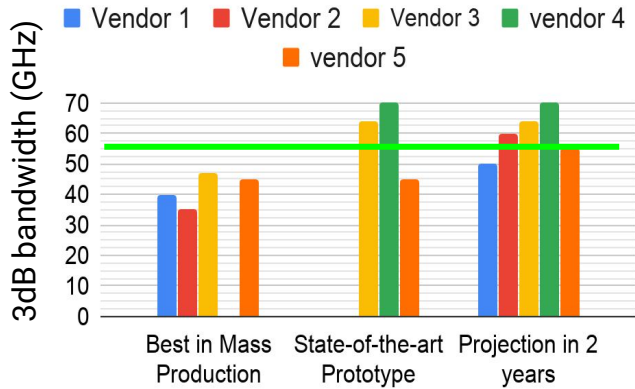
- Assume support both PAM4 and PAM6

- **Prototype:** 2 vendor meet the preliminary guideline requirements for cooled EML
- **2-year projected:** 1 vendor meet the preliminary guideline requirements for uncooled EML

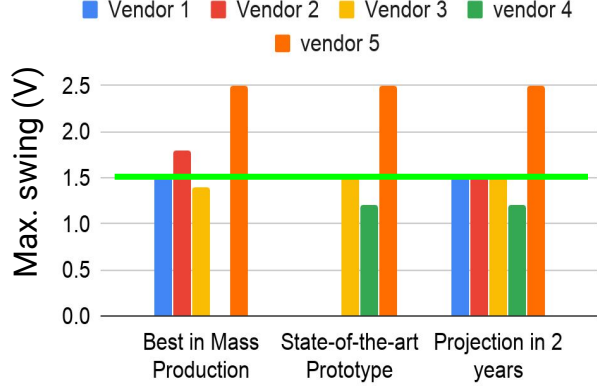
200Gb/s per optical lane components survey

Transmitter 1 : EML Driver

3-dB Bandwidth



Drive swing

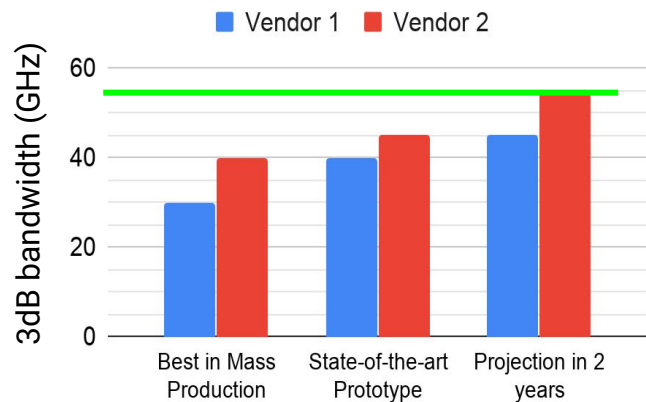


- **Prototype:** 1 vendor meets the preliminary guideline requirements
- **2-year projected:** 3 vendors meet the preliminary guideline requirements

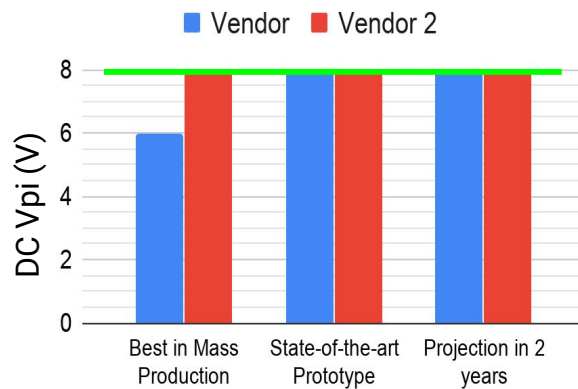
200Gb/s per optical lane components survey

Transmitter 2: SiP-MZM

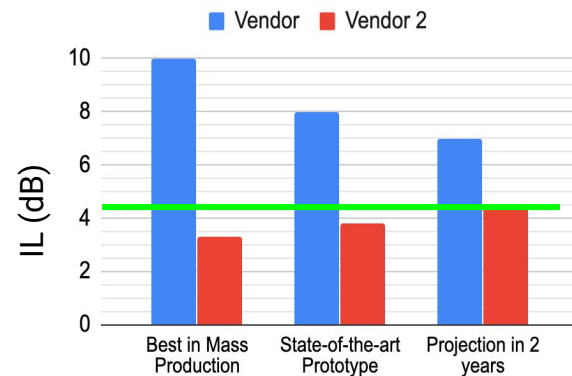
3-dB Bandwidth



DC Vpi



Insertion loss (dB)

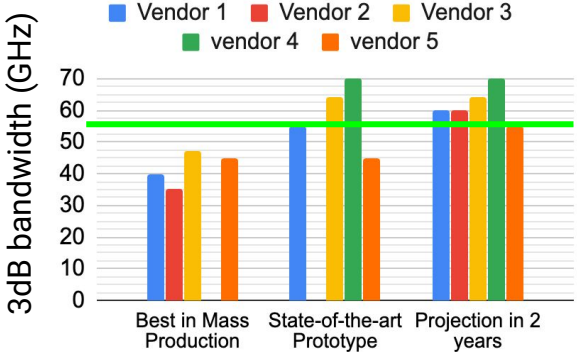


- **2-year projected:** 1 vendor meets the preliminary guideline requirements for DR reach

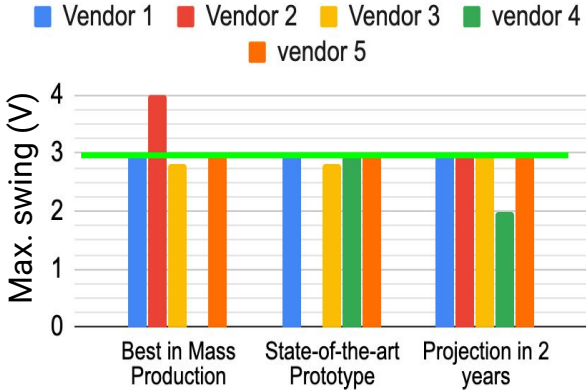
200Gb/s per lane components survey

Transmitter 2: SiP-MZM driver

3-dB Bandwidth



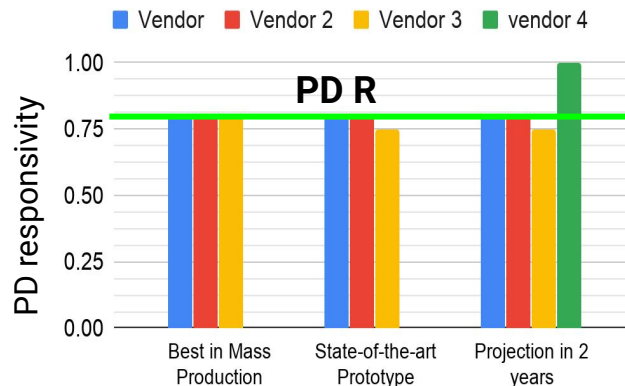
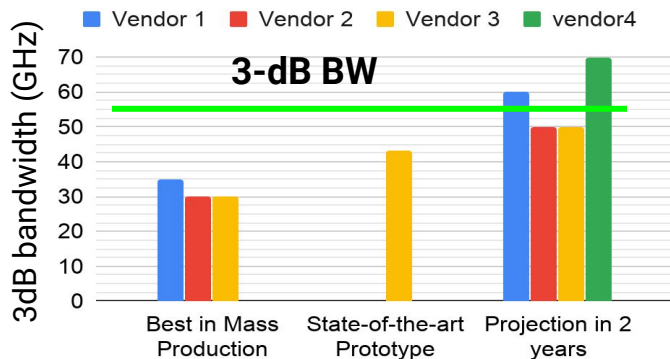
Drive output swing



- **Prototype:** 2 vendor meets the preliminary guideline requirements
- **2-year projected:** 4 vendors meet the preliminary guideline requirements

200Gb/s per optical lane components survey

Receiver: PD+TIA

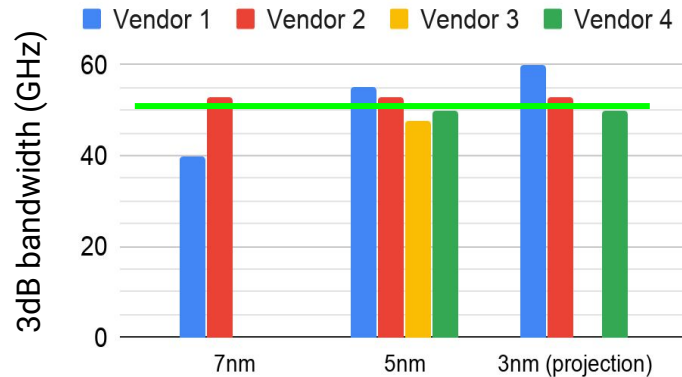


- **2-year projected:** 2 vendor meet the preliminary guideline requirements

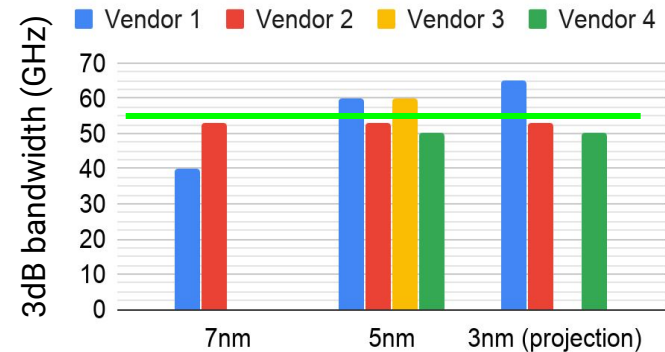
200Gb/s per optical lane components survey

Digital Electronics: CMOS DAC and ADC

DAC



ADC



- **Prototype:** 2 vendor meets the preliminary BW guideline requirements

200Gb/s per Optical Lane Components Readiness

For 500m DR4 and 1km CWDM4

		Mass Production	Prototype	2-year Projected
Transmitter 1 InP EML	InP EML	✗	✓ (cooled)	✓ (uncooled)
	EML Driver	✗	✓	✓
Transmitter 2 SiP MZM	MZM (SiPh)	✗	✗	Ready for DR-reach
	MZM Driver	✗	✓	✓
Receiver	PD / TIA	✗	✗	✓
Electronics	CMOS DSP	✗ (7nm)	✓ (5nm)	✓ (5nm/3nm)

Conclusions

- Demands for datacenter bandwidths keep growing quickly.
- It is right time to develop the next higher-speed Ethernet beyond 400GbE
- For intra-datacenter applications, 200Gbps per lane IM-DD implementation provides:
 - Lower TCO
 - Pathway to 1.6Tbps Ethernet
- Technical feasibility of 200Gbps per optical lane is within the reach in the next two years
 - Well within the time frame to complete the next higher-speed Ethernet standard